

High-Performance and Industrially Viable Nanostructured SiO_x Layers for Interface Passivation in Thin Film Solar Cells

José M. V. Cunha,* Kevin Oliveira, Jackson Lontchi, Tomás S. Lopes, Marco A. Curado, João R. S. Barbosa, Carlos Vinhais, Wei-Chao Chen, Jérôme Borme, Helder Fonseca, João Gaspar, Denis Flandre, Marika Edoff, Ana G. Silva, Jennifer P. Teixeira, Paulo A. Fernandes, and Pedro M. P. Salomé

Herein, it is demonstrated, by using industrial techniques, that a passivation layer with nanocontacts based on silicon oxide (SiO_x) leads to significant improvements in the optoelectronic performance of ultrathin $\text{Cu}(\text{In,Ga})\text{Se}_2$ (CIGS) solar cells. Two approaches are applied for contact patterning of the passivation layer: point contacts and line contacts. For two CIGS growth conditions, 550 and 500 °C, the SiO_x passivation layer demonstrates positive passivation properties, which are supported by electrical simulations. Such positive effects lead to an increase in the light to power conversion efficiency value of 2.6% (absolute value) for passivated devices compared with a nonpassivated reference device. Strikingly, both passivation architectures present similar efficiency values. However, there is a trade-off between passivation effect and charge extraction, as demonstrated by the trade-off between open-circuit voltage (V_{oc}) and short-circuit current density (J_{sc}) compared with fill factor (FF). For the first time, a fully industrial upscalable process combining SiO_x as rear passivation layer deposited by chemical vapor deposition, with photolithography for line contacts, yields promising results toward high-performance and low-cost ultrathin CIGS solar cells with champion devices reaching efficiency values of 12%, demonstrating the potential of SiO_x as a passivation material for energy conversion devices.

1. Introduction

Over the past decades, silicon wafer-based technology has been dominating the photovoltaic (PV) market, with thin film technology being a competitor with a relatively small market share.^[1] Thin film technology is invariably looking to build up its competitiveness in the PV market, which will require innovative strategies to simultaneously increase performance and decrease production costs. $\text{Cu}(\text{In,Ga})\text{Se}_2$ (CIGS)-based solar cells with a typical 2 μm absorber layer thickness stand out from its commercially available thin film counterparts, CdTe and amorphous silicon, presenting the highest light to power conversion efficiency value of all three technologies (23.35%).^[2,3] To pursue a prominent position in the market, a possible path is to further decrease the CIGS thickness to the ultrathin range (significantly lower than 1000 nm), where the most efficient devices in that range have a light to power conversion efficiency value of 11.8% for a 240 nm-thick,^[4] 15.2% for a 490 nm-thick,^[5] and

J. M. V. Cunha, K. Oliveira, T. S. Lopes, M. A. Curado, J. R. S. Barbosa, Prof. C. Vinhais, Dr. J. Borme, H. Fonseca, Dr. J. Gaspar, Dr. J. P. Teixeira, Prof. P. A. Fernandes, Prof. P. M. P. Salomé
INL – International Iberian Nanotechnology Laboratory
Avenida Mestre José Veiga, Braga 4715-330, Portugal
E-mail: jose.cunha@inl.int

J. M. V. Cunha, Prof. P. M. P. Salomé
Departamento de Física
Universidade de Aveiro
Campus Universitário de Santiago, Aveiro 3810-193, Portugal

J. M. V. Cunha, Prof. P. A. Fernandes
i3N
Universidade de Aveiro
Campus Universitário de Santiago, Aveiro 3810-193, Portugal

Dr. J. Lontchi, Prof. D. Flandre
ICTEAM Institute
Université Catholique de Louvain
Place du Levant 3, Louvain-la-Neuve 1348, Belgium

T. S. Lopes
Institute for Material Research (IMO)
Hasselt University (Partner in Solliance)
Agoralaangebouw H, Diepenbeek 3590, Belgium

T. S. Lopes
IMEC Division IMOMEC (Partner in Solliance)
Wetenschapspark 1, Diepenbeek 3590, Belgium

T. S. Lopes
EnergyVille
Thorpark, Poort Genk 8310 & 8320, Genk 3600, Belgium

M. A. Curado
Department of Physics
CFisUC
University of Coimbra
Coimbra P-3004-516, Portugal

 The ORCID identification number(s) for the author(s) of this article can be found under <https://doi.org/10.1002/solr.202000534>.

DOI: 10.1002/solr.202000534

17.5% for a 900 nm-thick^[6] CIGS devices. The CIGS thickness reduction from the standard 2 μm to the ultrathin range will allow for a reduction in production costs by increasing machine throughput.^[7,8] Moreover, the thickness reduction is in line with the recommendations from a recently conducted CIGS PV installations life cycle assessment study that encourages a continuous reduction on the rare metals usage,^[9] thus allowing for lower production costs and also lower environmental impact. From a device performance point of view, keeping the conventional architecture with an ultrathin CIGS layer raises new optoelectronic concerns. Deterioration of the short-circuit current density (J_{sc}) values is consistently observed in ultrathin devices when compared with standard-thick ones.^[10,11] In ultrathin devices, the thickness required for a complete optical absorption is effectively higher than the CIGS absorber layer thickness, leading to significant absorption losses in the near-infrared region (NIR). To overcome such optical losses, different light management schemes have been implemented.^[12–16] However, the complexity of the CIGS optoelectronic properties and architecture of the device turns the integration of efficient novel designs into the CIGS solar cells challenging. A reduction of the CIGS layer thickness from the standard-thick to the ultrathin range will lead to a decreased charge carrier's mean path and an increased minority carrier generation rate per unit volume.^[17] Accordingly, an increased charge carrier concentration is observed, which will potentially allow for an open-circuit voltage (V_{oc}) increase.^[17] Nonetheless, it will also increase the minority charge carrier's likelihood of reaching the rear contact, increasing the probability of recombination at this interface.^[18] One approach to mitigate the recombination in the rear CIGS surface is focused on the use of an insulator passivation layer, in between the rear contact and the CIGS layer.^[18,19,20–28] To establish electrical contact between CIGS and the rear electrode, nanocontacts are opened in the insulator layer, with e-beam lithography being commonly used.^[4,18,19,29] However, photolithography has the advantage of being cheaper and to have higher machine throughput compared with e-beam lithography. The referred advantages are highly desired for industrial processes, and, therefore, the photolithographic process upscalability to the industry has the potential to be straightforward.

Several insulator materials, e.g., Al_2O_3 , Si_3N_x , SiO_x , TiO_2 , to name but a few, have been studied as passivation layers in the CIGS technology.^[20,25,30–33] The prospect of using the same approach and insulator to passivate both front and rear interfaces of the same solar cell is very attractive from a fabrication perspective, and SiO_x emerges as a strong material to perform such role.^[20,30,34] SiO_x presents promising properties that allow for

its implementation as front and rear passivation layers, namely, the ability to change the polarity values of the fixed insulator charges (Q_f) by manipulating the deposition parameters, enabling an efficient field-effect passivation of both minority and majority CIGS charge carriers.^[30] It is even possible to change the density of interface active defects and the Q_f density, which is proven to be an essential parameter to accomplish a high-performance passivation layer.^[35] Furthermore, SiO_x rear passivation used with photolithography to open the nanocontacts has already been implemented with promising preliminary results.^[20] Nonetheless, more comprehensive studies are necessary to understand and establish an effective procedure to implement SiO_x as a passivation layer in the CIGS solar cells architecture. Furthermore, SiO_x has the potential to be used as a passivation layer in other thin film technologies, such as CdTe , $\text{Cu}_2\text{ZnSnS}_4$ (CZTS), or perovskites, which could allow for an effective defect passivation.^[36–47]

In this study, point contacts and line contacts are used to implement two different SiO_x rear passivation architectures for CIGS-based solar cells, with the intention of attaining high-performance substrates. The point contacts will be produced by a laboratory e-beam lithography technique and the line contacts will be produced by an industrially viable photolithography technique. The use of two different patterning techniques is of utmost importance in this work because the main objective is to understand if photolithography has the potential to produce devices with the same performance as e-beam lithography. Furthermore, the two passivated substrates are compared between them and against a conventional nonpassivated substrate. The reference nonpassivated device will be named as Ref, and passivated devices will be named as PointContact or LineContact following the respective passivation architecture. We note that to better comprehend the passivation layer effect on the performance increase compared with the conventional nonpassivated substrate, the CIGS layer was not optimized, i.e., it did not use Ga profile, postdeposition treatment (PDT), or antireflective coating, so that the gains observed for the passivated substrates are effectively and only due to the passivation effect itself. The three substrates are integrated in CIGS-based solar cells fabricated at 550 °C (standard temperature) and 500 °C. Therefore, it is possible to better understand the ability of the SiO_x layer to survive different CIGS growth temperatures, and, at the same time, determine if it retains its passivation properties. The integration of both passivated substrates in the CIGS solar cells architecture delivers an increase in the figures of merit compared with the conventional solar cell substrate. Electrical simulations coupled with morphological, structural,

Prof. C. Vinhais
Departamento de Física
Instituto Superior de Engenharia do Porto
Instituto Politécnico do Porto
Porto 4200-072, Portugal

Dr. W.-C. Chen, Prof. M. Edoff
Ångström Laboratory
Solid State Electronics
Ångström Solar Center
Uppsala University
Uppsala SE-751 21, Sweden

Prof. A. G. Silva
Departamento de Física
Faculdade de Ciências e Tecnologia
CEFITEC
Universidade Nova de Lisboa
Campus de Caparica, Lisbon 2829-516, Portugal

Prof. P. A. Fernandes, Prof. P. M. P. Salomé
Departamento de Física
CIETI
Instituto Superior de Engenharia do Porto
Instituto Politécnico do Porto
Porto 4200-072, Portugal

and electrical characterizations of the fabricated devices are presented, allowing for an in-depth study of the SiO_x rear passivation properties on CIGS solar cells.

2. Characterization

In this work, CIGS was grown at two different temperatures, 550 and 500 °C, which will bring relevant insights into 1) the SiO_x ability to survive the harsh CIGS growth conditions (see the scanning electron microscopy [SEM] analyses in the Supporting Information), and 2) the SiO_x performance as a passivation layer for each of the studied temperatures. Such study is needed as it is known that some materials, such as SiO_x , do not maintain its properties at elevated temperatures.^[48] The current density

versus voltage (J - V) figures of merit suggest that devices grown at 550 °C have a higher optoelectronic performance with higher V_{oc} , fill factor (FF), and light to power conversion efficiency values, compared with respective devices grown at 500 °C, as shown in **Figure 1a**. The Ref device grown at 550 °C achieved an average efficiency value of 8.8%, whereas the equivalent device grown at 500 °C attained an average efficiency value of 6.2%. Looking to the average V_{oc} values, it decreases from 585 to 523 mV, from Ref grown at 550 and 500 °C, respectively, with FF values also decreasing from 66.9% to 50.2%. The figures of merit value increase for the Ref grown at 550 °C is possibly related with better morphological and structural properties, due to 1) larger CIGS grains with less grain boundaries, resulting in the higher CIGS growth temperature, as observed by SEM in the Supporting Information and as it was already reported in

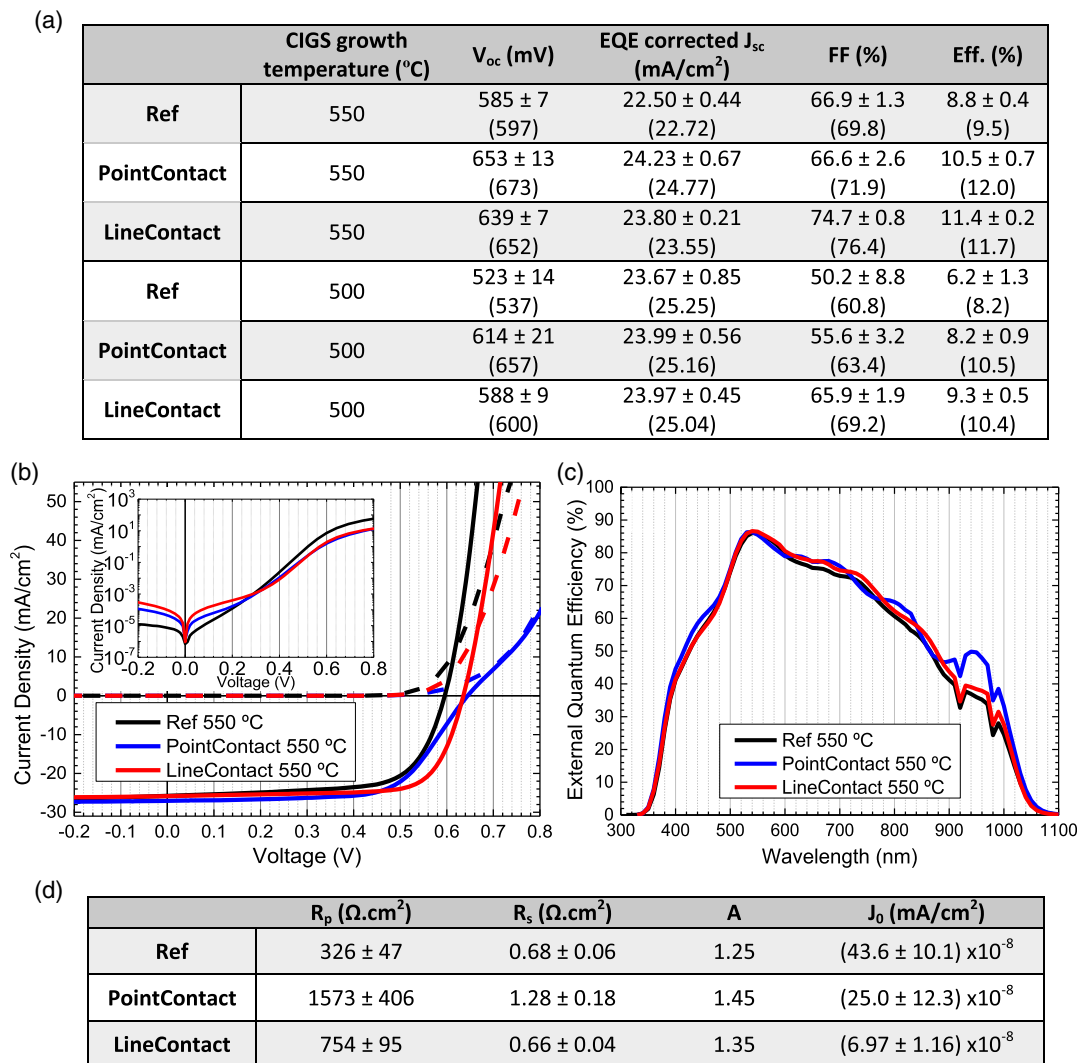


Figure 1. a) J - V figures of merit: averages and standard deviations values of all studied devices. Figures of merit values for the highest efficiency cells also presented in brackets. J_{sc} values calculated from the EQE spectra. Averages taken from 12 cells; b) representative J - V plots of the device with the efficiency value closer to the efficiency average value. Straight lines are illuminated curves and dashed lines are dark curves. The inset figure is the dark log J - V curve; c) representative EQE plots of the device with the J_{sc} value closer to the J_{sc} average value; and d) solar cells' diode parameters average and standard deviation values for devices grown with a substrate temperature of 550 °C. R_p stands for parallel resistance, R_s for series resistance, A for ideality factor, and J_0 for saturation current density.

the literature;^[49–51] and other effects such as 2) Ga depth distribution;^[52,53] or 3) alkali dynamics,^[49,54–57] to name but a few examples. The passivated devices grown at 500 °C demonstrated the same electrical trends as the ones grown at 550 °C, with all the SiO_x patterned devices having superior V_{oc} and efficiency values compared with the respective reference device. The V_{oc} increase is a clear indication that the insulator layer SiO_x acts as an effective rear passivation layer for CIGS solar cells. An important observation is that the SiO_x passivation effect is independent of the CIGS growth temperature, as shown by the improved figures of merit values of the passivated devices compared with the respective reference counterparts, as shown in Figure 1a. As similar trends were obtained for both temperatures, and for clarity, only detailed results of devices grown at 550 °C will be analyzed henceforth. Therefore, only J – V plots measured under dark and illumination (Figure 1b), external quantum efficiency (EQE) plots (Figure 1c), and diode parameters (Figure 1d) for the devices grown at 550 °C are shown and analyzed. The figures of merit of all studied devices (Figure 1a) are still shown for a better understanding of the effective SiO_x passivation effect at different temperatures.

The J – V plots of the Ref and LineContact devices show a crossover between dark and illuminated curves,^[58] as shown in Figure 1b. Such behavior is possibly related with an illumination-dependent voltage drop on a thin defect layer located on the CIGS absorber front surface.^[59,60] PointContact device does not show a clear crossover because a rollover behavior appears.^[58] In CIGS solar cells, a rollover has been observed when a rear sodium (Na) diffusion barrier is present.^[55,61,62]

The PointContact device achieves a V_{oc} average value of 653 mV, which corresponds to a 68 mV increase over the Ref, and an average 10.5% in power conversion efficiency values. Moreover, the respective PointContact champion cell attains an efficiency value of 12.0%. From the EQE curves, shown in Figure 1c, the J_{sc} increase over Ref is mostly localized in the NIR. The LineContact device achieves an average V_{oc} value of 639 mV, which corresponds to a 54 mV increase over the Ref. LineContact does not have the rollover seen in the PointContact, which is translated into the highest average FF value of 74.7% among the studied devices. As a result, LineContact device has the highest average efficiency value of 11.4%, which is 2.6% (abs.) higher than Ref. It is observed that even though LineContact device has a higher average efficiency value compared with PointContact device, the latter has a higher champion cell efficiency value, which is explained by a higher inhomogeneity, as observed by its higher standard deviation value. Regarding the inhomogeneity observed for the PointContact device, from the process point of view, it is more complex to produce holes with 150 nm than lines with 1100 nm. As we are producing structures with a small diameter (150 nm), even though they are fabricated by the very well-established e-beam lithography process, the variation within the substrate will be higher compared with the lines produced by the industrial photolithography process. Therefore, it is shown that the LineContact process provides better homogeneity of the features throughout the substrate compared with the PointContact process.

The devices' diode parameters are shown in Figure 1d. The possibility of shunt paths, common in ultrathin devices,^[10,11,21,63]

is reduced by the insulator used in the passivation layer, resulting in an increase in the parallel resistance (R_p) values of both PointContact and LineContact compared with the Ref device. PointContact presents a higher series resistance (R_s) compared with other devices possibly due to a reduced rear contact opening area, limiting carrier collection, which results in charge losses. Therefore, there is room for further optimization of the rear passivation configuration in the point contact architecture. On the contrary, devices with line contact configuration have a higher contact area compared with PointContact devices, leading to a lower R_s average value. The shown rollover for the PointContact device, which is affecting its FF values, is also affecting the ideality factor (A) value, as the PointContact device has the highest A value among the studied devices. The PointContact device shows higher V_{oc} values than LineContact, which is attributed to the higher SiO_x passivation area. The increased V_{oc} values over the reference device indicate an effective interface defects passivation by the SiO_x layer for both passivation patterns, which is more pronounced for the device with the highest passivation area. The V_{oc} value increase is supported by the decrease in the saturation current density (J_0) value for both passivated devices compared with Ref (Figure 1d), strengthening the proof of the effectiveness of the rear interface passivation by the SiO_x passivation layer. Therefore, it is demonstrated the good SiO_x passivation, as the passivated device's V_{oc} and J_0 values indicate a lower recombination rate compared with the reference device.^[64,65]

It is necessary to understand the Na effect on the devices' performance, and if the figures of merit value increase is only related with passivation effects and/or Na effects as well. Therefore, glow-discharge optical emission spectroscopy (GDOES) measurements were conducted to measure the in-depth Na profile for devices grown at 550 °C, as shown in Figure 2a. To better understand the Na concentration influence together with the SiO_x passivation effect on each device's optoelectronic properties, dark capacitance versus voltage (C – V) measurements were conducted to get the net free carriers concentration (N_{cv}) and depletion region width (W) values for each device at the 0 V bias.^[33,66,67] A representative N_{cv} against W plot, with varying bias, for each device, is shown in Figure 2b with the N_{cv} and W average and standard deviation values shown in the inset table of Figure 2b. It is noted that the shown plot for each device is a representative curve, which might have different N_{cv} and W values compared with the respective average values presented in the inset table.

Analyzing the Mo/CIGS interface represented by the dashed line in Figure 2a, it is clear that SiO_x forms a Na accumulation layer, where the PointContact architecture acts as a stronger Na accumulation layer than the LineContact, which is the repercussion of the significantly lower contact area of the PointContact compared with the LineContact architecture. Having in mind that for the passivation layers 15 nm NaF precursors layers were used as the Na source—a thickness value equal to the one of 2000 nm CIGS—it is hard to understand if such Na accumulation is evidence of a diffusion barrier behavior of in-diffusion (from the NaF into the Mo) or out-diffusion (from the glass to the CIGS). At a specific depth, it is observed a slightly Na concentration increase for the PointContact device, compared with the other studied devices, as represented by the circle in

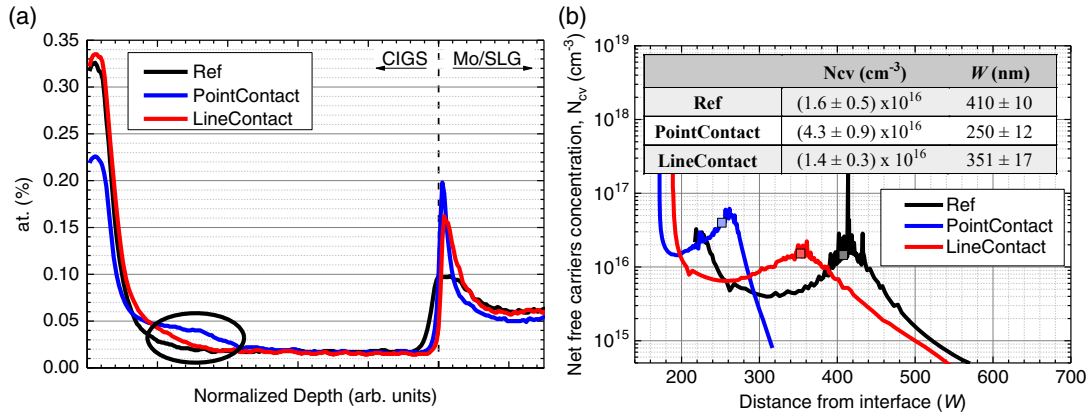


Figure 2. a) GDOES Na in-depth profile of devices grown with a substrate temperature of 550 °C. The dashed vertical line is a guide to the eye representing where the CIGS/Mo interface is located; and b) representative N_{cv} versus W plot of the device with the N_{cv} and W values closer to the N_{cv} and W average values. The depletion region and net free carrier concentration are taken at 0 V and are represented in square marks. Inset table represents the zero-bias average and standard deviation values of N_{cv} and W . Averages taken from 12 cells.

the graph. To understand which device has the highest Na concentration overall, secondary ion mass spectrometry (SIMS) measurements should be conducted.^[68]

In Figure 2b, it is shown that PointContact has the highest N_{cv} value of $4.3 \times 10^{16} \text{ cm}^{-3}$, while the LineContact and Ref have approximately the same N_{cv} value. Ref device has the highest depletion region among the studied devices. The N_{cv} values are known to increase with Na concentration,^[55,69] which is in accordance with the N_{cv} values extraction at 0 V bias being matched to the region in the Figure 2a represented by a circle for the PointContact device. However, the N_{cv} values extraction at 0 V bias may have been extracted at a slightly higher depth values for both Ref and LineContact devices (considering the higher average W values for these two devices comparing with PointContact one, as shown in the inset table of Figure 2b) where both have approximately the same Na concentration (lower than PointContact). Therefore, the N_{cv} value increase for the PointContact should be related with the highest Na concentration observed for a specific region, compared with Ref and LineContact devices. The high passivation area in the PointContact device had a clear impact in the Na distribution in the CIGS layer.

3. Electrical Simulations

Electrical simulations were performed to better understand the presented results and to study the SiO_x performance as a passivation layer. Kotipalli et al.^[31] analyzed metal–insulator–semiconductor (MIS) devices before and after annealing at $\approx 500^\circ\text{C}$ with selenium atmosphere to reproduce the CIGS growth. It was shown that the polarity of the Q_f values changed from positive (before exposure) to negative (after exposure).^[31] Despite of the insulator in the study being alumina (Al_2O_3), the same phenomenon may be expected for the SiO_x case because previous MIS studies without annealing also demonstrated positive charges in the SiO_x insulator.^[30] Therefore, based on the previous studies, it was decided to simulate both SiO_x possible Q_f polarity signals, to better comprehend its impact on the devices' performance and to show the importance of the Q_f

values control during the insulator deposition to maximize the final devices' performance. Q_f values of $+4 \times 10^{11}$ and $-8 \times 10^{12} \text{ cm}^{-2}$ were studied.^[30,31] Such values were chosen to understand if the SiO_x layer has the ideal Q_f values, which should be around 10^{12} – 10^{13} cm^{-2} or if the material has a Q_f value below the ideal one $\approx 10^{11} \text{ cm}^{-2}$, as reported in the literature.^[31,70,71] The contact width values were varied, and for a better understanding, the contact width values were converted into a percentage of passivation area using the following equations^[72]

$$\text{Passivation area} = \left[1 - \frac{(\pi d^2)}{4P^2} \right] \times 100 \quad (1)$$

$$\text{Passivation area} = \left[1 - \left(\frac{d \times P}{P \times P} \right) \right] \times 100 \quad (2)$$

where d is the contact width value and P is the pitch value. Equation (1) is for point contact architectures and Equation (2) is for line contact architectures. The electrical simulations demonstrate V_{oc} , J_{sc} , FF, and absolute efficiency gains of the passivated devices over the reference device, as shown in **Figure 3**. In this simulation, the presented gains are in comparison with a simulated nonpassivated reference device, i.e., a gain equal to 0 represents the same performance as the reference device.^[35]

The electrical simulations show that the solar cells performance optimization depends on the studied parameters, such as the Q_f value and respective polarity value, as well as the contact shape and passivation area. Negative Q_f values, represented by square marks in the graphs, show superior performance in all figures of merit compared with positive Q_f values, and therefore only negative Q_f values will be analyzed henceforth. Considering negative Q_f values, the V_{oc} and J_{sc} values follow the same trend. Moreover, both figures of merit increased with higher passivation areas, as shown in Figure 3a,b. Such increase is expected because, for higher passivation areas, the effective rear recombination rate is reduced. On the contrary, FF values, shown in Figure 3c, have the opposite trend with values increasing for lower passivation areas. FF values are negatively affected by

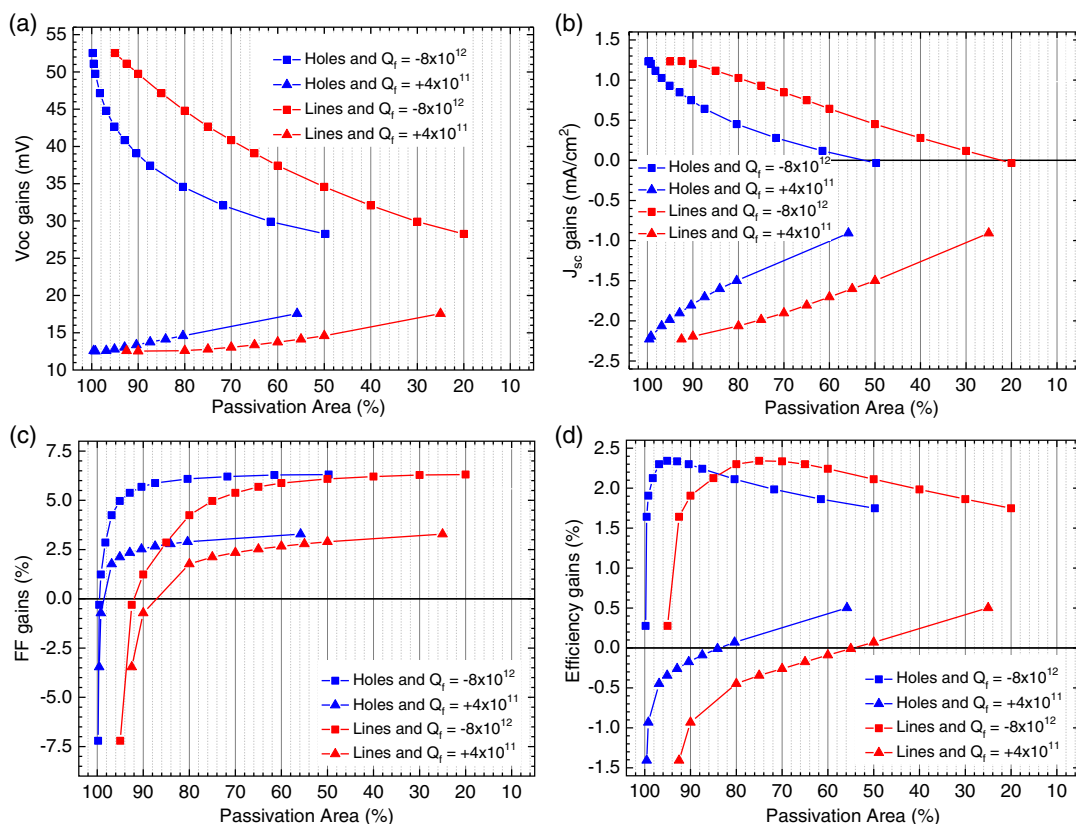


Figure 3. Figures of merit absolute gains of the passivated devices over the reference device: a) V_{oc} gains, b) J_{sc} gains, c) FF gains, and d) efficiency gains. Pitch value of 2000 nm simulated. Red lines correspond to the passivation area for line contacts and blue lines correspond to the passivation area for point contacts. Square marks represent a Q_f value of $-8 \times 10^{12} \text{ cm}^{-2}$ and triangle marks represent a Q_f value of $+4 \times 10^{11} \text{ cm}^{-2}$.

the contact opening width because the FF values degrade when the contact opening is reduced and does not allow for efficient current extraction. Therefore, the FF values will increase when the contact area is increased, i.e., for reduced passivation area, and tend to saturate after the contact area is sufficiently large. Regarding efficiency gains (Figure 3d), this simulation shows that the optimum passivation area value for a passivation architecture with point contacts, represented by blue lines in the graph, is approximately 95%. In contrast, the optimum value for a passivation architecture with line contacts, represented by a red line in the graph, is approximately 75%. Such striking simulation results show the need to carefully design the passivation architecture, depending on the used contact shape, to account for the optimal structure dimensions, in order to achieve the highest performance values. In our case, the PointContact device passivation area (99.7%) has surpassed the optimal values, which translates into an efficiency drop and, according to the simulations, it is mainly due to FF losses. Therefore, the passivation area should be reduced to allow for effective charge collection. The LineContact device has less passivation area (59.5%) than the found optimal values, which translates into a shortcoming in the efficiency value and, according to the simulations, it is mainly due to V_{oc} and J_{sc} losses. A remarkable outcome can already be considered: a line contact passivation area of 75% is equivalent in terms of efficiency gains ($\approx 2.4\%$) to a point contact passivation architecture with 95% of passivation area.

4. Discussion

In this work, two different patterns were successfully produced on a SiO_x layer to be used as a rear passivation layer in ultrathin CIGS solar cells. Furthermore, two different CIGS deposition temperature values were tested to understand the resilience of the SiO_x passivation effect. Differences between the CIGS layers grown at 550 and 500 °C were found both at the grain and crystalline level, and are shown in detail by SEM and X-ray diffraction (XRD) analyses in the Supporting Information. Electrical measurements show that devices with point contacts, that have higher passivation area, presented increased V_{oc} values over devices with line contacts. On the contrary, the LineContact device that has higher contact area has increased FF values over the PointContact device. The lower FF values for the PointContact device compared with the LineContact device observed in the J - V measurements were supported by electrical simulations, which demonstrated that the PointContact device has room for further improvement by increasing the contact area, which will allow for increased FF values. The highest Na diffusion barrier effect observed in GDOES for PointContact device might suggest that PointContact device does not have an optimized Na concentration. Considering such hypothesis, the highest Na diffusion barrier effect observed in GDOES for PointContact devices supports the observed rollover in the J - V analysis, as the rollover might be related with the Na diffusion barrier.

The observed rollover also explains the low average FF value of PointContact device, as well as its high standard deviation value. The PointContact ideality factor parameter value is also affected by the rollover appearance, as it is the highest value among the studied devices. Despite the observed Na barrier for the passivated devices, all devices had a Na predeposition treatment. However, the amount of deposited sodium fluoride (NaF) does not seem to be optimized for the used CIGS thickness and/or passivation architecture—as evidenced by the strong Na accumulation at the interfaces and the odd FF values indicating that a more efficient Na introduction strategy needs to be developed. GDOES measurements may have matrix effects that may cause artifacts to appear,^[73] and, therefore, the absolute quantity of Na and its distribution on the CIGS layer should not be considered by GDOES measurements alone. Consequently, to further understand the effect of the passivation layer on the Na distribution in the CIGS and the effects on final devices, more measurements, such as SIMS, X-ray photoelectron spectroscopy (XPS), Rutherford backscattering spectrometry (RBS), and particle-induced X-ray emission (PIXE), should be conducted to complement the GDOES measurement.^[74–78]

LineContact devices have higher collection area compared with PointContact devices, resulting in higher FF values in the J – V analysis, which ultimately results in the highest average efficiency values of the studied devices. Nonetheless, it was found that LineContact devices have lower V_{oc} values compared with PointContact devices due to a lower passivation area. Electrical simulations explain these results and show that LineContact devices have room for further improvement by increasing the passivation area, which will lead to higher V_{oc} values.

Comparing the illuminated and dark J – V measurements, it is observed that while the illuminated R_p value is lower for the Ref compared with PointContact and LineContact devices, the current density for Ref device observed in the dark J – V plot at -0.2 V is the lowest among the studied devices. The reason for the differences between the dark and light J – V plots is a complex topic, but it may be due to the light-soaking treatment performed before the illuminated J – V measurements, which was not performed before the dark J – V measurements. Such differences may be related with light-induced defects.^[79–81] Moreover,

even though the Ref device has the lowest R_p value together with the highest J_0 value, such parameters could not be physically correlated because they are extracted in different voltage regions and related to different operations. The PointContact device on its hand has the highest R_p value, but it does not have the lowest J_0 value. In the C – V analysis, it was shown that the LineContact device has approximately the same N_{cv} value compared with Ref, and that the PointContact device has the highest N_{cv} average value of $4.3 \times 10^{16} \text{ cm}^{-3}$. A possible hypothesis to explain the result is related with the region represented by a circle in Figure 2a, where the PointContact device has the highest Na concentration compared with the studied devices. Therefore, the highest N_{cv} value for the PointContact device is related with the Na concentration and distribution, as it is known that the N_{cv} values increase for devices with higher Na concentration.^[55,69] However, it is not clear if the increase in the N_{cv} values fully explains the V_{oc} increase for the PointContact device. Therefore, it is necessary to calculate the expected V_{oc} gain that is provided by the N_{cv} increase for the passivated devices compared with Ref. Such V_{oc} gain provided by the N_{cv} value increase will be hereafter named as ΔV_{oc} . To calculate ΔV_{oc} , the following equation was used^[18,82,83]

$$\Delta V_{oc} = \frac{k_B T}{q} \ln \left(\frac{N_{cv}(\text{passivated})}{N_{cv}(\text{reference})} \right) \quad (3)$$

where k_B is the Boltzmann constant, T is the temperature, and q is the electron charge. For the calculation, the N_{cv} values from Figure 2b were used. So, considering N_{cv} values, PointContact device has an expected V_{oc} gain of 26 ± 10 mV over Ref. Note that this value reflects the region where this device should have the higher Na value and consequently the higher N_{cv} value. The LineContact is not expected to have a V_{oc} gain related to N_{cv} because both PointContact and Ref devices have, within experimental variation, the same N_{cv} value and very similar Na distribution trends. In Figure 4, it demonstrated, for all devices, the V_{oc} gains that are related with the N_{cv} (ΔV_{oc}) and the V_{oc} gains that are not related with N_{cv} , which, for example, could be related with passivation effects. Moreover, it is also shown the thermodynamic losses and the V_{oc} deficit for each device. Therefore, the lower V_{oc} deficit of the passivated devices compared with

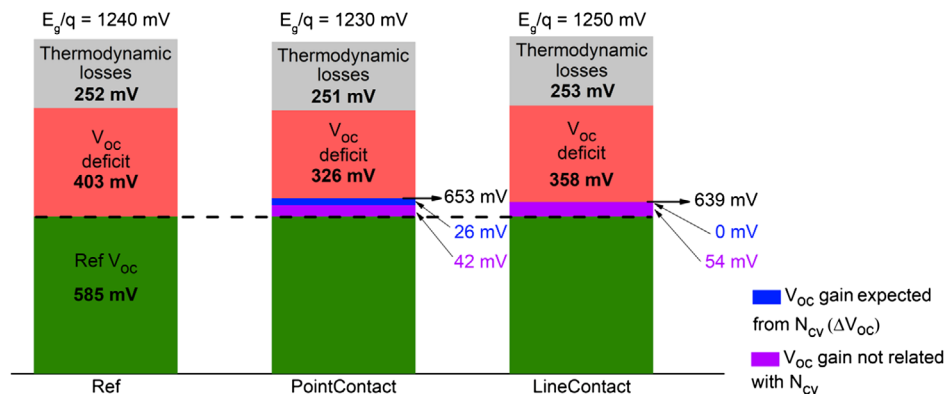


Figure 4. Passivated devices V_{oc} gains over the Ref device. The devices bandgap value is presented on top of each column. It is represented in red the V_{oc} deficit, in green the V_{oc} of the Ref device, in blue the calculated ΔV_{oc} , and in purple the V_{oc} gain not related with N_{cv} . The measured V_{oc} of each device is also presented.

the Ref device cannot be fully explained by its N_{cv} value, highlighting that the lower V_{oc} deficit is likely due to the passivation effects. In Figure 4, it is not considered the V_{oc} losses in our devices that are related to 1) potential fluctuations;^[84–89] 2) the used Ga profile;^[52,53,90–92] 3) the lack of PDT;^[93–98] and 4) the lack of a front passivation layer,^[70,99–102] to name but a few potential V_{oc} losses. However, these losses should be roughly the same for the three devices.

PointContact has a V_{oc} gain measured from J – V analysis of 68 mV over Ref, which has a difference of 42 mV compared with the calculated ΔV_{oc} . The complete V_{oc} gain is, therefore, not explained by the increased N_{cv} values. Thus, other effects, such as the passivation from the SiO_x layer, are also playing a role. To further corroborate such hypothesis, one has to look to LineContact device as well. For this device, a ΔV_{oc} value of 0 mV was obtained. Nonetheless, the effective V_{oc} gain from J – V measurements was 54 mV over Ref. Therefore, the Na concentration and, consequently, the N_{cv} influence are clearly not enough to explain the V_{oc} increase seen in J – V and the chemical and/or field-effect passivation may be playing a vital role in increasing the V_{oc} values of the studied passivated devices.

Electrical simulations showed the importance to control charge density and polarity inside the insulator for optimal solar cells performance. Considering the PointContact devices' passivation area and the measured J – V figures of merit gains over the reference device, namely, V_{oc} gain of 68 mV, J_{sc} gain of 1.7 mA cm^{-2} , same FF, and efficiency gain of 1.7%, one can infer the Q_f values present in the SiO_x layer by analyzing Figure 3. Considering such values for a passivation area of 99.7% in Figure 3, the Q_f values inside the SiO_x insulator are negative, and they may be approximately $-8 \times 10^{12} \text{ cm}^{-2}$, which is an expected value for good field-effect passivation.^[31,70,71] For a 59.5% line contact passivation area and considering the observed J – V figures of merit for this device, the same conclusions from the PointContact device may be achieved, which states that the SiO_x has a high density of negative Q_f values of $\approx -8 \times 10^{12} \text{ cm}^{-2}$. Therefore, the Q_f values are apparently the same for both architectures, which was expected, because the Q_f is directly related with the insulator used as passivation layer, as well as the interface with the absorber layer, which, in this case, is also the same for both architectures. The negative charges are preferred for rear passivation and the high density of fixed charges is correlated with the increase in the field-effect passivation strength. Note that to accurately calculate the Q_f values present in the SiO_x layer, MIS devices will have to be fabricated with exactly the same SiO_x layer as the solar cells, but without contact holes or lines, as shown elsewhere.^[30] This could be a future target. However, previous simulations have shown that the exact Q_f and surface recombination velocity (SRV) values have limited influence on the cell performances once they achieve sufficiently good values, i.e., negative Q_f and low SRV.^[35] Otherwise, positive Q_f or high SRV would reduce the efficiency values of the passivated cells below the reference ones, contrarily to our observations.

The demonstrated good field-effect and/or chemical passivation effects observed by electrical simulations and J – V measurements allow SiO_x to be considered an effective choice for CIGS solar cells rear passivation.

5. Conclusions

The obtained results suggest that SiO_x deposited by the high throughput and industrial technique chemical vapor deposition is an effective insulator to be used for rear interface passivation of CIGS solar cells. Ultrathin devices with SiO_x , independently of the passivation pattern and CIGS growth temperature used, show superior optoelectronic performance compared with their respective nonpassivated counterparts. The beneficial passivation effects of SiO_x allowed for an increased J – V figures of merit over the reference nonpassivated device in ultrathin CIGS solar cells.

LineContact devices that used photolithography, which is a widely used industrial technique, show promising results with a champion cell achieving a light to power conversion efficiency value of 11.7% and an increase in the average efficiency value of 2.6% in comparison with a nonpassivated reference device. The PointContact devices that in this work were still processed using e-beam lithography achieved a champion cell of 12.0%. Surprisingly, these two patterns show a compromise between V_{oc} , J_{sc} , and FF connected to passivation area, and our simulations show that the studied architectures have room for further improvement, which will allow to further increase efficiency values. Therefore, the patterns shown in this work do not have ideal dimensions, as shown by the simulations, but prove that the industrially viable photolithographic device has the potential to reach the e-beam device performance. Moreover, the effects of the studied architectures for alkali introduction were discussed on the basis of GDOES measurements, highlighting the fact that a new strategy for Na introduction must be implemented. In the future, for a better understanding of this problematic, SIMS, XPS, RBS, and PIXE should also be conducted together with GDOES, to understand the passivation layer architecture implication on the alkali distribution in the CIGS layer. Such experiments should also be strongly supported by simulations to comprehend the implications on the final solar cells devices.

The results presented here demonstrate that future improvements to the passivation pattern design can lead to even higher optoelectronic performance of the passivation structure due to a better compromise between charge extraction and passivation area, demonstrating the potential of SiO_x as a passivation material for energy conversion devices. The results of this work show that widely used microelectronics processes, such as SiO_x deposited using chemical vapor deposition together with photolithography, will allow for the upscaling of the passivation layer for industrial CIGS devices. Moreover, the SiO_x layer presented here can be further used in CdTe, kesterite, and perovskite solar cells, as well as in other energy-related applications, such as solid-state batteries, thermoelectrics, and other devices that use complex materials.

6. Experimental Section

The substrates consist of $5 \times 5 \text{ cm}^2$ Soda-Lime Glass (SLG) with a 350 nm layer of Mo deposited by sputtering on top of the SLG. The passivation layer fabrication procedure (Figure 5) begins by growing a SiO_x layer, 18 nm thick, by plasma-enhanced chemical vapor deposition (PECVD) using a SPTS MPX PECVD tool at 13.56 MHz and 300 °C. The point contact pattern is accomplished using e-beam lithography. The substrate is coated with 430 nm of polymethyl methacrylate (PMMA) resist. Then, an exposure is performed through e-beam lithography using a Vistec EBPG 5200 tool. The exposed resist is developed

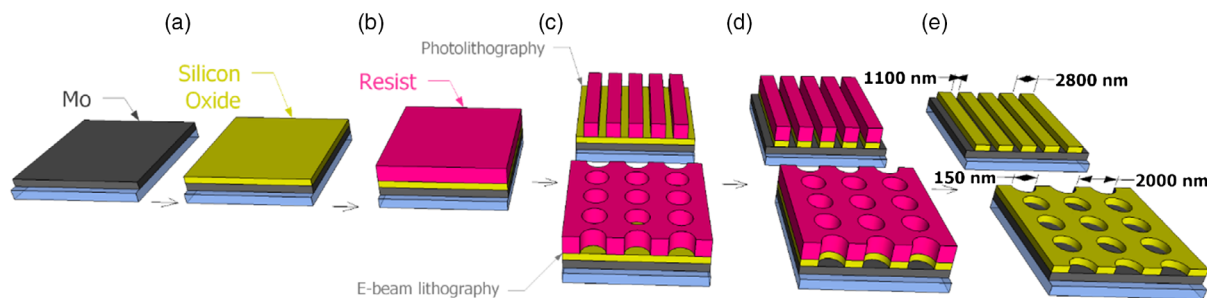


Figure 5. Photolithography and e-beam lithography step-by-step processes. The different processes are represented by a) insulator deposition; b) resist coating (AZ1505 for photolithography or PMMA for e-beam lithography); c) exposure; d) etching; and e) resist removal. The last image of each process has the final substrate features: photolithographic substrate with a width of 1100 nm and pitch of 2800 nm; and e-beam substrate with a width of 150 nm and pitch of 2000 nm. Images not at scale.

by methyl isobutyl ketone (MIBK) developer. Subsequently, the exposed insulator is etched by reactive ion etching (RIE) using a SPTS ICP. The remaining resist is removed by immersing the substrates in an ultrasound bath with acetone for 30 min followed by a 5 min bath in deionized water. The accomplished pattern has a point contact structure with holes diameter of 150 and 2000 nm pitch.

Line contacts are patterned using photolithography where the substrate is coated with 600 nm of a positive photoresist, AZ1505. The line contact pattern is then exposed by a 405 nm laser, using a Direct Write Laser tool (Heidelberg Instruments DWL 2000). The exposed photoresist is developed by an AZ 400 K 1:4 developer. The remaining fabrication processes, etching and resist removal, followed the same conditions as the ones for the e-beam substrate. The accomplished pattern has a line contact structure with a line width of 1100 and 2800 nm pitch.

Regarding the used patterns, we want to point out that it is not timely and cost viable to produce lines by e-beam lithography. On the contrary, it is difficult to produce holes by photolithography with less than 1000 nm, due to the laser resolution.

The $5 \times 5 \text{ cm}^2$ substrates were divided in two $2.5 \times 5 \text{ cm}^2$ pieces to grow different CIGS layers in the same substrate architecture. Prior to the CIGS layer growth, a 15 nm layer of NaF is evaporated onto all substrates. The CIGS growth is performed using a one-stage coevaporation process,^[18,103,104] with a flat evaporation rate, in two runs: 1) CIGS growth at 550 °C, used in this work as reference CIGS growth temperature as this is the conventional temperature used,^[20-22,29] with an estimated CIGS thickness of 710 nm and composition values of $[\text{Cu}]/([\text{Ga}] + [\text{In}]) = 0.83 \pm 0.01$ and $[\text{Ga}]/([\text{Ga}] + [\text{In}]) = 0.40 \pm 0.02$; and 2) CIGS growth at a lower temperature of 500 °C with an estimated CIGS thickness of 710 nm and composition values of $[\text{Cu}]/([\text{Ga}] + [\text{In}]) = 0.83 \pm 0.01$ and $[\text{Ga}]/([\text{Ga}] + [\text{In}]) = 0.39 \pm 0.02$ as determined by X-ray fluorescence (XRF) performed in a Panalytical Epsilon 5. After growing the CIGS layer, the process follows the Ångström baseline.^[103] The final solar cell devices are defined by scribing with an area of 0.5 cm^2 . The final substrates/devices are referred according to the names present in Table 1. The reference nonpassivated device is named as Ref, and passivated devices are named as PointContact or LineContact following the respective passivation architecture.

A Bruker Icon atomic force microscope (AFM) was used in tapping mode with a scan rate of 1 Hz for line contacts and 0.5 Hz for point contacts. Sodium compositional analyses were performed with GDOES for in-depth profiling in combination with XRF for average in-depth composition.

Complete solar cells were characterized by AM1.5 illuminated and dark $J-V$, and EQE measurements performed in home-built systems. Illuminated $J-V$ and EQE measurements were performed after light soaking at AM1.5 during 20 min with the substrate temperature being kept at 20 °C. EQE measurements were performed at 0 V bias. It is noted that the diode parameters A and J_0 were acquired from the dark curve, and the parameters R_p and R_s were acquired from the illuminated curve, according to Hegedus et al.^[64] The $J-V$ figures of merit average and standard deviation values were taken from all available solar cells in each sample,

Table 1. Names of the substrates/devices used according to the passivation architecture.

	CIGS growth temperature [°C]	SiO _x nanocontact lithography
Ref	550/500	–
PointContact	550/500	E-beam
LineContact	550/500	Photolithography

which in our case are 12 solar cells. Moreover, the raw data obtained from the $J-V$ measurements are presented in the Supporting Information together with $J-V$ curves for all devices. The presented efficiency values were calculated using the EQE corrected J_{sc} values, which is a standard procedure for ultrathin CIGS solar cells.^[10,13,20,29,104-106] $C-V$ dark measurements were performed using a precision LCR meter Agilent E4980 A with a 10 kHz frequency signal and a V_{RMS} of 25 mV. The bias applied ranged from -0.5 to 0.7 V. For the $C-V$ measurements, all 12 cells were measured and the data obtained from the N_{cv} and W analyses are presented in the Supporting Information together with $N_{cv}-W$ curves for all devices. Atypical cells were removed.

The presented plots for each measurement always have in consideration a representative solar cell, and the choice is based on the average measurement value, i.e., the solar cell with the studied parameter closer to its average value is considered to be the representative one.

The electrical properties of a 710 nm-thick CIGS device were simulated using the Silvaco ATLAS 2D program, as specified elsewhere.^[35] The crucial parameters used were contact resistance (R_c), bulk defect density, rear reflectance (R_b), doping density, and SRV at the rear interface. To approach reality, the SRV value has been differentiated for the two rear interfaces Mo/CIGS and SiO_x/CIGS. All the used parameter values are shown in Table 2. The default R_c value of $0.1 \Omega \text{ cm}^2$ used for the passivated devices represents an equivalent series resistance of $1 \Omega \text{ cm}^2$ in our 2D

Table 2. Crucial parameter values used in Silvaco ATLAS 2D electrical simulations. It is noted that for the passivated devices, it is represented the SRV value inside the nanocontacts (Mo/CIGS) and outside the nanocontacts (SiO_x/CIGS).

	R_c [$\Omega \text{ cm}^2$]	Defect density [cm^{-3}]	R_b [%]	Doping density [cm^{-3}]	SRV [cm s^{-1}]
Ref	1	2×10^{14}	20	3×10^{16}	Mo/CIGS 1×10^7
PointContact	0.1	1×10^{14}	45	5×10^{16}	Mo/CIGS 1×10^7 SiO _x /CIGS 1×10^2
LineContact	0.1	1×10^{14}	45	5×10^{16}	Mo/CIGS 1×10^7 SiO _x /CIGS 1×10^2

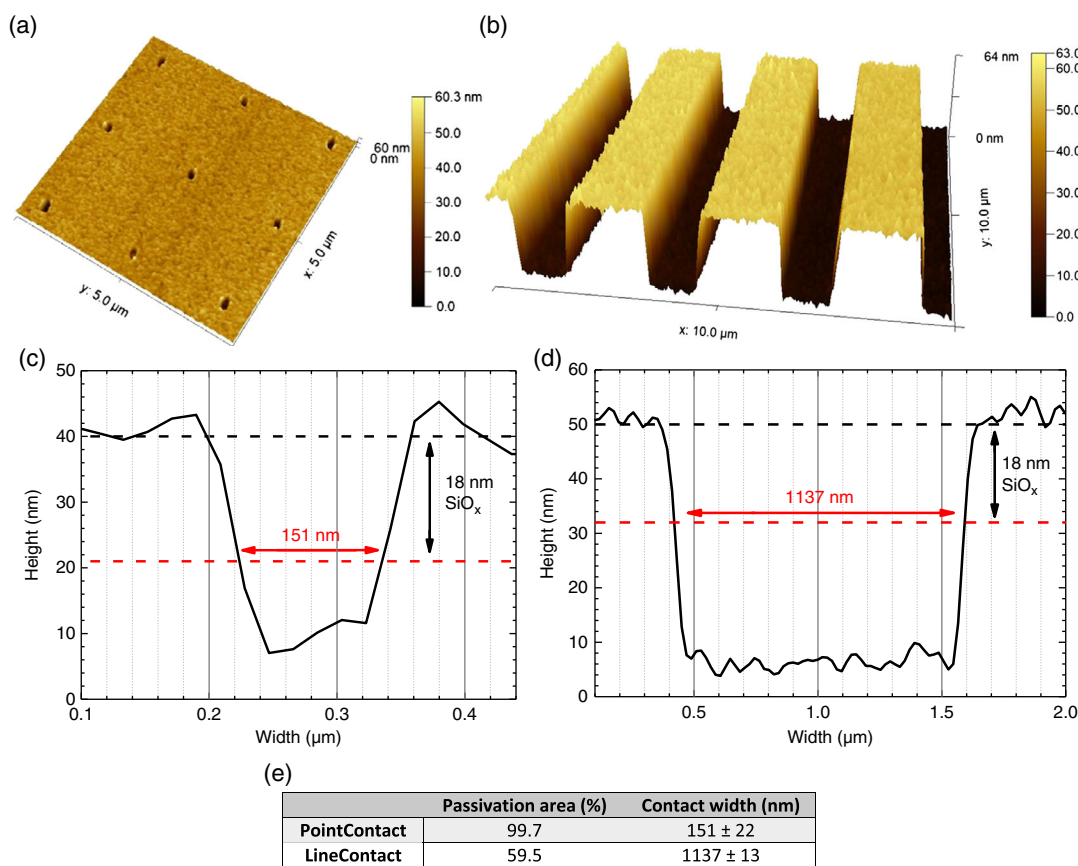


Figure 6. Representative AFM 3D image of a) point contact and b) line contact based substrates. Representative AFM cross-sectional plot of c) point contact d) line contact based substrates, where the SiO_x thickness (double black arrow) and the average contact width (double red arrow) are shown; and e) contact width average and standard deviation values of both studied substrate architectures. Average values were taken in nine patterns of the same AFM image. The passivation area for each device is also presented. Representative AFM images of the substrates were chosen based on the contact width value closer to the average contact width value.

model, identical to the reference device, as described elsewhere.^[35] The R_c value accounts for the resistance in the nanocontact openings for the passivated devices, scaled by the width to pitch ratio of the opening,^[35] i.e., assuming by default an average width to pitch ratio of 0.1 as the same for both structures. The presented defect density is related to bulk midgap acceptor defects.^[35] The chosen R_b values were based on optical simulations,^[35] whereas the doping density values were based on experimental data.^[35] The simulations were conducted assuming the pitch value of 2000 and 2800 nm as obtained in the experiments. Nonetheless, as similar results were obtained, only simulations with a pitch value of 2000 nm were presented and analyzed.

Passivation Structure: AFM topography images were taken from all fabricated substrates. Figure 6a,b shows representative 3D AFM images of point and line contact substrates, respectively, showing well-defined vertical features for both cases. Figure 6c,d shows the AFM cross-sectional representative plot of a contact opening for each type of substrate architecture, from which the average value of the contact width was estimated (Figure 6e). In the cross-sectional plot, the double red arrow represents the average contact width, and it is established by considering the complete removal of the SiO_x layer with an 18 nm thickness.

The PointContact substrate resulted in contacts with an equivalent diameter average value of 151 nm, and the LineContact substrates resulted in line contacts with an average width value of 1137 nm. Average values were taken in nine patterns of the same AFM image. Therefore, according to Equation (1) and (2), the PointContact substrate resulted in a 99.7% of

passivated area, whereas the LineContact architecture allows for a 59.5% of passivated area, as shown in Figure 6e.

Supporting Information

Supporting Information is available from the Wiley Online Library or from the author.

Acknowledgements

Fundação para a Ciência e a Tecnologia (FCT) is acknowledged through the project IF/00133/2015, PD/BD/142780/2018, SFRH/BD/146776/2019, and UIDB/04730/2020. The European Union's Horizon 2020 research and innovation program ARCIQS-M project (grant agreement no. 720887) is acknowledged. This research was also supported by NovaCell—development of novel Ultrathin Solar Cell Architectures for low-light, low-cost, and flexible optoelectronic devices project (028075) cofunded by FCT and the ERDF through COMPETE2020. This research was supported by InovSolarCells—development of innovative nanostructured dielectric materials for interface passivation in thin film solar cells project (029696) cofunded by FCT and the ERDF through COMPETE2020.

Conflict of Interest

The authors declare no conflict of interest.

Data Availability Statement

The data that supports the findings of this study are available in the supplementary material of this article.

Keywords

Cu(In, Ga)Se₂, passivation, photolithography, silicon oxide, ultrathin

Received: September 1, 2020

Revised: January 12, 2021

Published online:

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